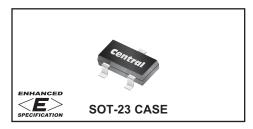
CMPT2907AE

ENHANCED SPECIFICATION SURFACE MOUNT PNP SILICON TRANSISTOR





www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT2907AE is an Enhanced version of the CMPT2907A PNP Switching transistor in a SOT-23 surface mount package, designed for switching applications, interface circuit and driver circuit applications.

MARKING CODE: C2FE

FEATURED ENHANCED SPECIFICATIONS:

- ♦ BV_{CBO} from 60V min to 90V min. (115V TYP)
- ♦ V_{CE(SAT)} from 1.6V max to 0.7V max. (0.280V TYP)
- ♦ hFF from 50 min to 75 min. (110 TYP)

MAXIMUM	RATINGS: (T _A =25°C)	SYMBOL			UNITS
♦ Collector-B	Base Voltage	V _{CBO}	9	0	V
Collector-Er	mitter Voltage	V_{CEO}	6	0	V
Emitter-Bas	e Voltage	V_{EBO}	5	.0	V
Continuous	Collector Current	IC	60	00	mA
Power Dissi	•	P_{D}		50	mW
	nd Storage Junction Temperature	T _J , T _{stg}		+150	°C
Thermal Re	sistance	$\Theta_{\sf JA}$	38	57	°C/W
	AL CHARACTERISTICS: (T _A =25°C u				
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
ICBO	V _{CB} =50V			10	nA
ICBO	V _{CB} =50V, T _A =125°C			10	μΑ
ICEV	V_{CE} =30V, V_{EB} =0.5V			50	nA
♦ BV _{CBO}	I _C =10μA	90	115		V
BVCEO	I _C =10mA	60			V
BV EBO	I _E =10μA	5.0			V
♦ V _{CE(SAT)}	I _C =150mA, I _B =15mA		0.103	0.2	V
♦ V _{CE(SAT)}	I _C =500mA, I _B =50mA		0.280	0.7	V
V _{BE(SAT)}	I _C =150mA, I _B =15mA			1.3	V
V _{BE} (SAT)	I _C =500mA, I _B =50mA			2.6	V
♦ h _{FE}	V _{CE} =10V, I _C =0.1mA	100	205		
hFE	V _{CE} =10V, I _C =1.0mA	100			
hFE	V _{CE} =10V, I _C =10mA	100			
h_{FE}	V _{CE} =10V, I _C =150mA	100		300	
♦ h _{FE}	V _{CE} =10V, I _C =500mA	75	110		
f_T	V_{CE} =20V, I_{C} =50mA, f=100MHz	200			MHz
C _{ob}	V_{CB} =10V, I_{E} =0, f =1.0MHz			8.0	pF
C _{ib}	V_{BE} =2.0V, I_{C} =0, f=1.0MHz			30	pF

♦ Enhanced specification

R2 (1-February 2010)

CMPT2907AE

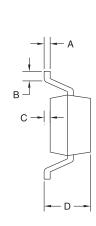


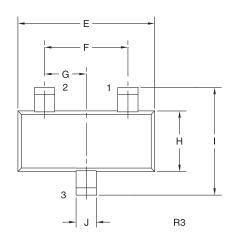


 $\textbf{ELECTRICAL CHARACTERISTICS - Continued:} \ (T_{A} = 25 ^{\circ}\text{C unless otherwise noted})$

,	SYMBOL	TEST CONDITIONS	MAX	UNITS
1	t _{on}	V_{CC} =30V, V_{BE} =0.5V, I_{C} =150mA, I_{B1} =15mA	45	ns
1	t _d	V_{CC} =30V, V_{BE} =0.5V, I_{C} =150mA, I_{B1} =15mA	10	ns
1	t _r	V_{CC} =30V, V_{BE} =0.5V, I_{C} =150mA, I_{B1} =15mA	40	ns
1	t _{off}	V _{CC} =6.0V, I _C =150mA, I _{B1} =I _{B2} =15mA	100	ns
1	t _s	V _{CC} =6.0V, I _C =150mA, I _{B1} =I _{B2} =15mA	80	ns
1	t _f	V _{CC} =6.0V, I _C =150mA, I _{B1} =I _{B2} =15mA	30	ns

SOT-23 CASE - MECHANICAL OUTLINE





LEAD CODE:

- 1) Base
- 2) Emitter
- 3) Collector

MARKING CODE: C2FE

DIMENSIONS								
	INCHES		MILLIMETERS					
SYMBOL	MIN	MAX	MIN	MAX				
Α	0.003	0.007	0.08	0.18				
В	0.006	-	0.15	-				
С	-	0.005	-	0.13				
D	0.035	0.043	0.89	1.09				
E	0.110	0.120	2.80	3.05				
F	0.075		1.90					
G	0.037		0.95					
Н	0.047	0.055	1.19	1.40				
	0.083	0.098	2.10	2.49				
J	0.014	0.020	0.35	0.50				
SOT-23 (REV: R3)								

R2 (1-February 2010)

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by Central Semiconductor manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H BC546/116 BC557/116 BSW67A NTE158 NTE187A NTE195A NTE2302 NTE2330 NTE63 C4460
2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA2126-E 2SB1204S-TL-E 2SD2150T100R SP000011176 FMMTA92QTA 2N2369ADCSM
2N5769 2SC2412KT146S 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E
US6T6TR NJL0281DG 732314D CMXT3906 TR CPH3121-TL-E CPH6021-TL-H 873787E IMZ2AT108 UMX21NTR MCH6102-TL-E
NJL0302DG 2N3583 2SA1434-TB-E 2SC3143-4-TB-E 2SD1621S-TD-E NTE103 30A02MH-TL-E NSV40301MZ4T1G NTE101 NTE13
NTE15 NTE16001